

Surface Mount - 400V - 800V > MAC12D, MAC12M, MAC12N

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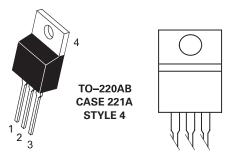
Description

Designed for high performance full-wave ac control applications where high noise immunity and commutating di/dt are required.

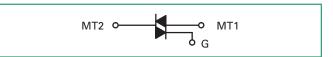
Features

- Blocking Voltage to 800 Volts
- On-State Current Rating of 12 Amperes RMS at 70°C
- Uniform Gate Trigger Currents in Three Quadrants, Q1, Q2, and Q3
- High Immunity to dv/dt 250 V/µs Minimum at 125°C
- Pisclaimer Notine information furnished is being and to be accurate and reliable. However, users test each product selected for their own applications. Littelfuse products are not designed for, and Disclaimer Notice at: www.littelfuse.com/disclaimer-electronics
- Industry Standard TO-220 Package

Pin Out



Functional Diagram



Additional Information









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Maximum Ratings $(T_J = 25^{\circ}C \text{ unless otherwise noted})$

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (Gate Open, Sine Wave 50 to 60 Hz, $T_J = 25^{\circ}$ to 100°C) MAC12D MAC12D	V RRM	400 600	V
MAC12N		800	
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_c = 70$ °C)	I _{T (RMS)}	12	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T _J = 125°C)	I _{TSM}	100	А
Circuit Fusing Consideration (t = 8.3 ms)	l²t	41	A ² sec
Peak Gate Power (Pulse Width $\leq 1.0 \mu s$, $T_t = 80^{\circ}C$)	P _{GM}	16	W
Average Gate Power (t = 8.3 ms , $T_{\text{C}} = 80^{\circ}\text{C}$)	P _{G (AV)}	0.35	W
Operating Junction Temperature Range	T _J	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Thermal Characteristics

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R _{8JC}	2.2 62.5	°C/W
Maximum Lead Temperature for Solderin 10 seconds	ng Purposes, 1/8" from case for	T_{L}	260	°C

^{1.} V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Thyristors

Electrical Characteristics - **OFF** $(T_j = 25^{\circ}\text{C unless otherwise noted}; \text{Electricals apply in both directions})$

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	$T_{J} = 25^{\circ}C$	l _{DRM} ,	-	-	0.01	m ^
$(V_D = V_{DRM} = V_{RRM}, Gate Open)$	T _J = 125°C	I _{RRM}	-	-	2.0	mA

Electrical Characteristics - **ON** $(T_J = 25^{\circ}\text{C unless otherwise noted; Electricals apply in both directions)$

Characteristic			Min	Тур	Max	Unit
Peak On–State Voltage (Note 2) ($I_{TM} = \pm 11 \text{ A}$)		V _{TM}	-	1.2	1.6	V
	MT2(+), G(+)		5.0	13	35	mA
Gate Trigger Current (Continuous dc)	MT2(+), G(-)	l _{GT}	5.0	13	35	
$(V_D = 12 \text{ V}, R_L = 100 \Omega)$	MT2(-), G(-)		5.0	13	35	
Holding Current ($V_D = 12 \text{ V}$, Gate Open, Initiating Current = ±150 mA))			-	20	40	mA
	MT2(+), G(+)	I _L	-	20	50	mA
Latching Current $(V_D = 24 \text{ V}, I_G = 50 \text{ mA})$	MT2(+), G(-)		_	30	80	
(1) 2.17.6 33.12.9	MT2(-), G(-)		_	20	50	
MT2(+), (0.5	0.78	1.5	
Gate Trigger Voltage $(V_D = 12 \text{ V}, R_L = 100 \Omega)$	MT2(+), G(-)	V _{GT}	0.5	0.70	1.5	V
	MT2(-), G(-)		0.5	0.71	1.5	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Indicates Pulse Test: Pulse Width \leq 2.0 ms, Duty Cycle \leq 2%.

Dynamic Characteristics

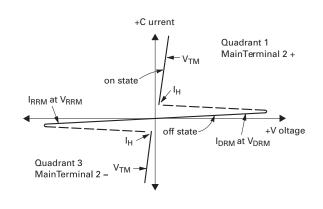
Characteristic		Min	Тур	Max	Unit
Rate of Change of Commutating Current See Figure 10. $(V_D = 400 \text{ V}, I_{TM} = 4.4 \text{ A}, \text{ Commutating dv/dt} = 18 \text{ V/}\mu\text{s}, \text{Gate Open}, T_J = 125 ^{\circ}\text{C}, f = 250 \text{ Hz}, \text{ No Snubber}) C_L = 10 \ \mu\text{F} \ L_L = 40 \ \text{mH}$		6.5	_	_	A/ms
Critical Rate of Rise of Off-State Voltage (V_D = Rated V_{DRM} , Exponential Waveform, R_{GK} = 510 Ω , T_J = 125°C)		500	_	-	V/µs
Repetitive Critical Rate of Rise of On-State Current IPK = 50 A; PW = 40 µsec; diG/dt = 200 mA/µsec; f = 60 Hz		-	-	10	A/µs

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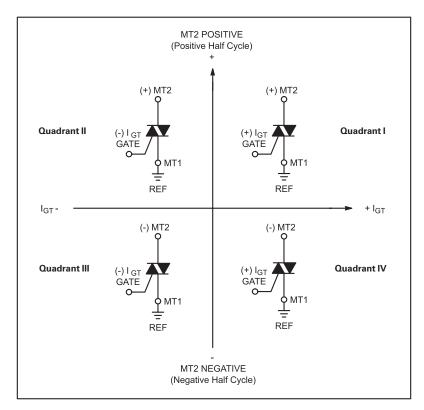
Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
I _H	Holding Current

Thyristors



Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.



Figure 1. Typical Gate Trigger Current vs Junction Temperature

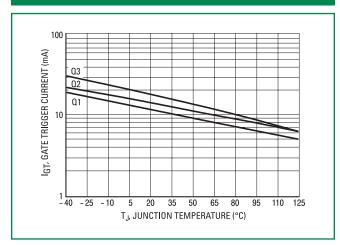


Figure 3. Typical Holding Current vs Junction Temperature

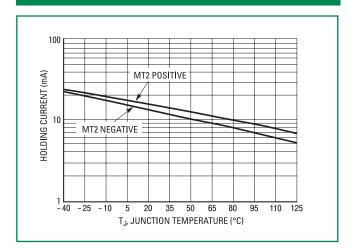


Figure 5. Typical RMS Current Derating

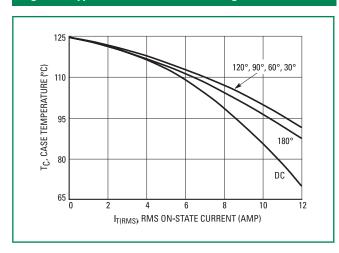


Figure 2. Typical Gate Trigger Voltage vs Junction Temperature

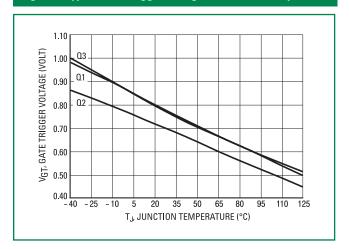


Figure 4. Typical Latching Current vs Junction Temperature

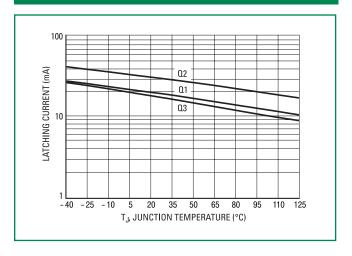
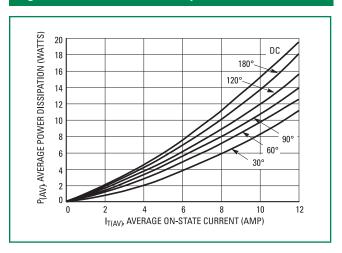
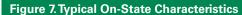
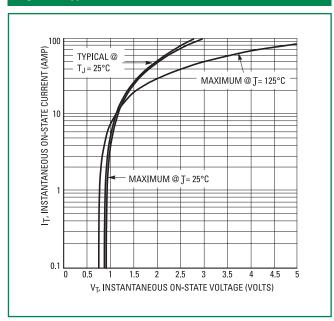


Figure 6. On-State Power Dissipation



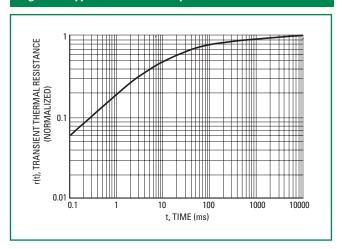




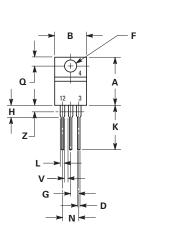


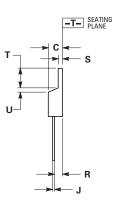
Thyristors

Figure 8. Typical Thermal Response



Dimensions

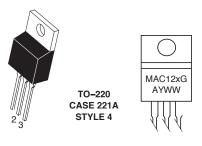




S :	Inches		Millim	neters
Dim	Min	Max	Min	Max
А	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

Part Marking System



 x=
 D, M, or N

 A=
 Assembly Location

 Y=
 Year

 WW
 = Work Week

 G
 = Pb-Free Package

Pin Assignment					
1	Main Terminal 1				
2	Main Terminal 2				
3	Gate				
4	Main Terminal 2				

Ordering Information

Device	Package	Shipping
MAC12DG		
MAC12MG	TO-220 (Pb-Free)	50 Units / Rail
MAC12NG		

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BTB16-600CW3G Z0410MF0AA2 Z0109MN,135 T825T-6I T1635T-6I T1220T-6I NTE5638 TYN612MRG TYN1225RG TPDV840RG
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